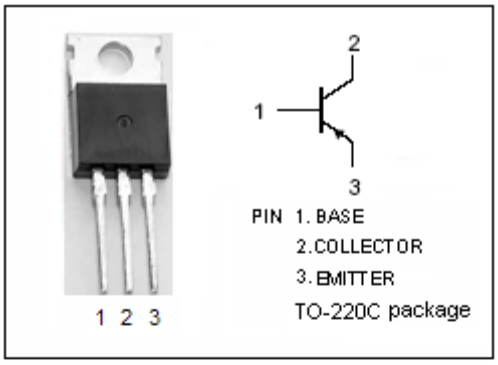
isc Silicon PNP Power Transistor 2SB925



DESCRIPTION

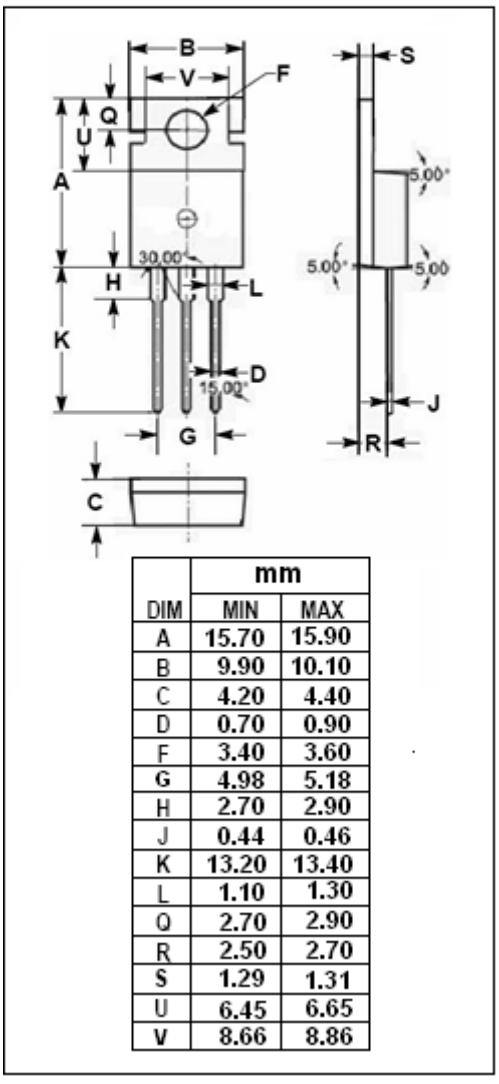
- High Collector Current:: I_C= -7A
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= -0.6V(Max)@I_C= -5A
- High Speed Switching

APPLICATIONS

- Designed for low voltage switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-12	A
P_C	Total Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; I_B= 0	-20			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.16A			-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -5A; I_B= -0.16A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-50	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-50	μA
h_{FE-1}	DC Current Gain	I_C= -0.1A; V_{CE}= -2V	45			
h_{FE-2}	DC Current Gain	I_C= -2A; V_{CE}= -2V	60		260	
C_{OB}	Collector Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1MHz		140		pF
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A; V_{CE}= -10V		150		MHz

Switching times

t_{on}	Turn-on Time	V_{CC}= -20V;I_C= -2A; I_{B1}= -I_{B2}= -66mA		0.1		μs
t_{stg}	Storage Time			0.5		μs
t_f	Fall Time			0.1		μs

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	90-180	130-260